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	Applicant(s): Kim et al.	
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U.S. PATENT DOCUMENTS

Examiner Initials	Document Number (Number-Kind Code)	Publication Date (MM-DD-YYYY)	Name of Patentee or Applicant	Class	Sub-class
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Examiner Initials	Document Number (Country Code-Number-Kind Code)	Publication Date (MM-DD-YYYY)	Name Of Patentee of Applicant	Translation? Yes/No/n/a
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pl	"Session 10/Low-Power & Communication Signal Processing/Paper FA10.3", Tadahi Kuroda et al.,
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pl	"Dynamic Leakage Cut-off Scheme for Low-Voltage SRAM's", Hiroshi Kawaguchi, et al., IEEE Symposium on VLSI Circuits Digest of Technical Papers, 1998, pp. 140-141

Examiner's Signature: <u>P. H. M. Kim</u>	Date Considered: <u>9/22/05</u>
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